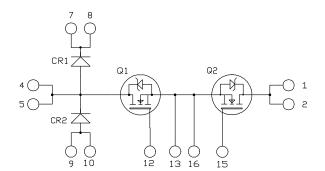
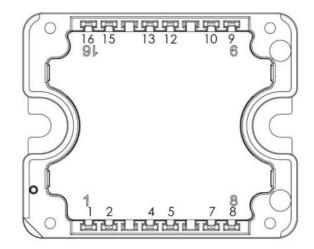


Vienna Rectifier SiC MOSFET Power Module

Product Overview

The MSCSM70VR1M19C1AG device is a Vienna rectifier 700V, 124A silicon carbide (SiC) power module.





Notes:

- Pins 1/2; 4/5; 7/8; 9/10 must be shorted together.
- All ratings at T_J = 25 °C, unless otherwise specified.

Δ CAUTION These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are the key features of MSCSM70VR1M19C1AG device:

- SiC Power MOSFET
 - Low R_{DS(on)}
 - High speed switching
 - Ultra low loss
- SiC Schottky Diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature independent switching behavior
 - Positive temperature coefficient on V_F
- Low stray inductance
- Kelvin source for easy drive
- Aluminum Nitride (AIN) substrate for improved thermal performance

Benefits

The following are the benefits of MSCSM70VR1M19C1AG device:

- Outstanding performance at high frequency operation
- · High-power and high-efficiency rectifiers and converters
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

Applications

The following are the applications of MSCSM70VR1M19C1AG device:

- Power factor correction
- Switched mode power supplies
- Uninterruptible power supplies

1. Electrical Specifications

The following sections show the electrical specifications of the MSCSM70VR1M19C1AG device.

1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings (per SiC MOSFET) of the MSCSM70VR1M19C1AG device.

Symbol	Parameter		Maximum Ratings	Unit
V _{DSS}	Drain-Source voltage		700	V
I _D	Continuous drain current $T_{C} = 25 \ ^{\circ}C$		124 ¹	A
		T _C = 80 °C	98 ¹	
I _{DM}	Pulsed drain current		250	
V _{GS}	Gate-Source voltage		-10/23	V
R _{DS(on)}	Drain-Source ON resistance		19	mΩ
PD	Power dissipation	T _C = 25 °C	365	W

Table 1-1. Absolute Maximum Ratings

Note:

1. Specification of SiC MOSFET device but output current must be limited due to size of power connectors.

The following table lists the electrical characteristics (per SiC MOSFET) of the MSCSM70VR1M19C1AG device.

 Table 1-2. Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0V; V _{DS} = 700V		-	_	100	μA
R _{DS(on)}	Drain-Source on	V _{GS} = 20V	T _J = 25 °C	—	15	19	mΩ
	resistance	I _D = 40A	T _J = 175 °C	_	18.8	_	
V _{GS(th)}	Gate threshold voltage	$V_{GS} = V_{DS}; I_D = 4 \text{ mA}$		1.9	2.4		V
I _{GSS}	Gate-Source leakage current	V _{GS} = 20V; V _{DS} = 0V		_	_	150	nA

Electrical Specifications

The following table lists the dynamic characteristics (per SiC MOSFET) of the MSCSM70VR1M19C1AG device.

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance	V _{GS} = 0V		_	4500	—	pF
C _{oss}	Output capacitance	V _{DS} = 700V	-	_	510	—	-
C _{rss}	Reverse transfer capacitance	f = 1 MHz		—	29	_	
Qg	Total gate charge	$V_{GS} = -5V/20V$		_	215	-	nC
Q _{gs}	Gate-source charge	V _{Bus} = 470V		_	58	_	
Q _{gd}	Gate-drain charge	I _D = 40A		_	35	-	
T _{d(on)}	Turn-on delay time	$V_{GS} = -5V/20V$	T _J = 150 °C	_	40	_	ns
Tr	Rise time	V _{Bus} = 400V			35	—	
T _{d(off)}	Turn-off delay time	I _D = 80A		_	50	_	
T _f	Fall time	R _{GON} = 27Ω R _{GOFF} = 4.7Ω			20	_	
Eon	Turn-on energy	$V_{GS} = -5V/20V$	T _J = 150 °C	_	545	_	μJ
E _{off}	Turn-off energy	V _{Bus} = 400V I _D = 80A R _{GON} = 27Ω R _{GOFF} = 4.7Ω	T _J = 150 °C	-	186	—	
R _{Gint}	Internal gate resistance			_	0.69	_	Ω
R _{thJC}	Junction-to-case therr	mal resistance		—	—	0.41	°C/W

Table 1-3. Dynamic Characteristics

The following table lists the body diode ratings and characteristics (per SiC MOSFET) of the MSCSM70VR1M19C1AG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V _{SD}	Diode forward voltage	V _{GS} = 0V; I _{SD} = 40A		3.4	—	V
		$V_{GS} = -5V; I_{SD} = 40A$	—	3.8	—	
t _{rr}	Reverse recovery time	I _{SD} = 40A		38	_	ns
Q _{rr}	Reverse recovery charge	$V_{GS} = -5V$		318	—	nC
I _{rr}	Reverse recovery current	V _R = 400V di _F /dt = 1000 A/μs	—	14.8	—	A

Electrical Specifications

1.2 SiC Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the SiC diode ratings and characteristics of the MSCSM70VR1M19C1AG device.

Table 1-5. SiC Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
V _{RRM}	Peak repetitive reverse volt	age		_	—	1200	V
I _{RM}	Reverse leakage current	V _R = 1200V	T _J = 25 °C	_	15	200	μA
			T _J = 175 °C	_	250	—	
I _F	DC Forward current		T _C = 100 °C	_	50	—	А
V _F	Diode forward voltage	I _F = 50A	T _J = 25 °C	_	1.5	1.8	V
			T _J = 175 °C		2.1	—	
Q _C	Total capacitive charge	V _R = 600V		_	224	—	nC
С	Total capacitance	f = 1 MHz, V _R =	400V	—	246	—	pF
		f = 1 MHz, V _R =	800V	_	182		
R _{thJC}	Junction-to-case thermal re	sistance		_	—	0.56	°C/W

Electrical Specifications

1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM70VR1M19C1AG device.

Symbol	Characteristic	Min.	Max.	Unit		
V _{ISOL}	RMS isolation voltage, any terminal to ca	RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz				V
TJ	Operating junction temperature range	Operating junction temperature range			175	°C
T _{JOP}	Recommended junction temperature und	Recommended junction temperature under switching conditions			T _{Jmax} –25	
T _{STG}	Storage temperature range			-40	125	
T _C	Operating case temperature			-40	125	
Torque	Mounting torque	Mounting torque To heatsink M4				N.m
Wt	Package weight			_	80	g

Table 1-6. Thermal and Package Characteristics

Electrical Specifications

1.4 Typical SiC MOSFET Performance Curve

The following figures show the SiC MOSFET performance curves of the MSCSM70VR1M19C1AG device.

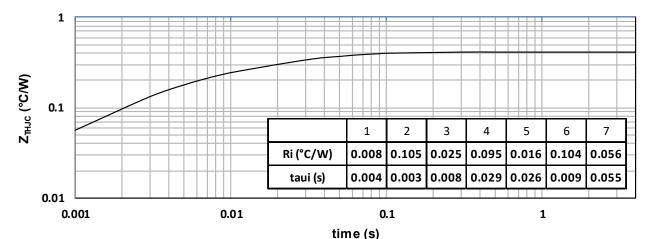
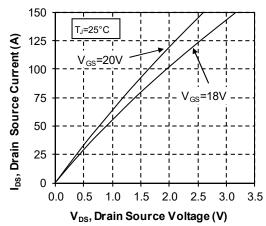


Figure 1-1. Maximum Thermal Impedance







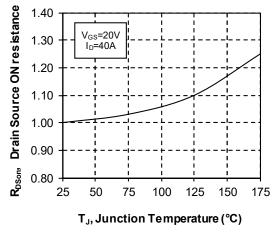
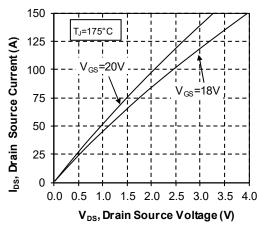
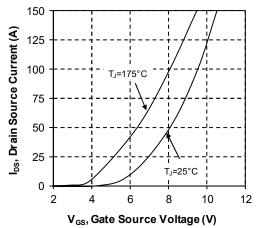


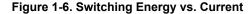
Figure 1-3. Output Characteristics, T_J = 175 °C

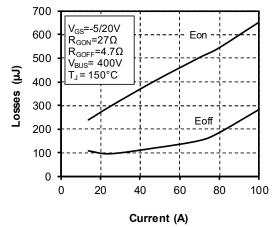


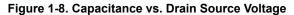




Electrical Specifications







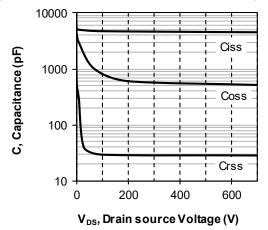


Figure 1-10. Body Diode Characteristics, T_J = 25 °C

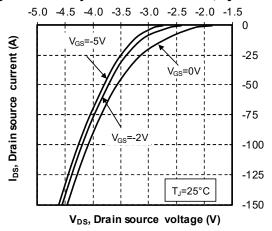


Figure 1-7. Turn On Energy vs. Rg

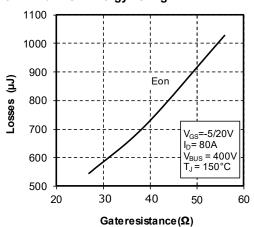


Figure 1-9. Gate Charge vs. Gate Source Voltage

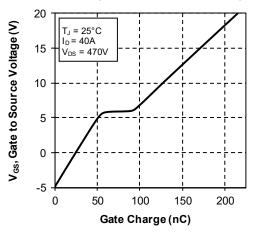
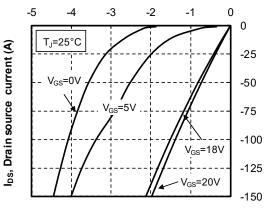
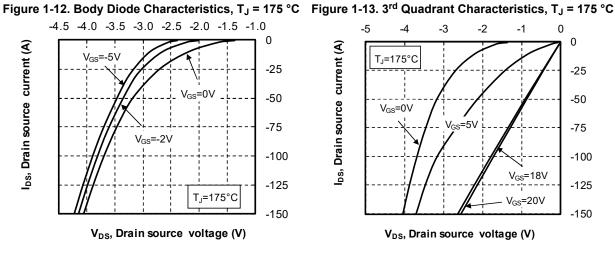


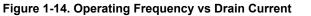
Figure 1-11. 3rd Quadrant Characteristics, T_J = 25 °C



V_{DS}, Drain source voltage (V)

Electrical Specifications





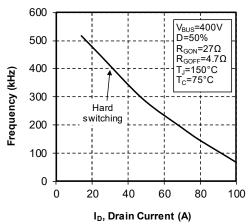
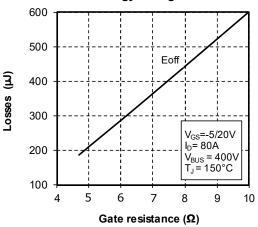


Figure 1-15. Turn Off Energy vs. Rg



1.5 Typical SiC Diode Performance Curve

The following figures show the SiC diode performance curves of the MSCSM70VR1M19C1AG device.

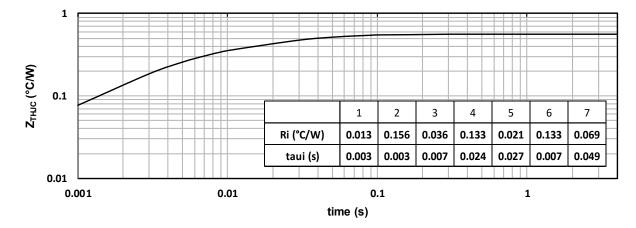


Figure 1-16. Maximum Thermal Impedance



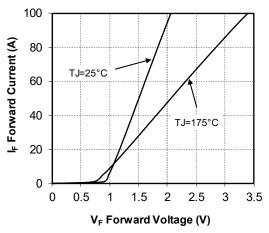
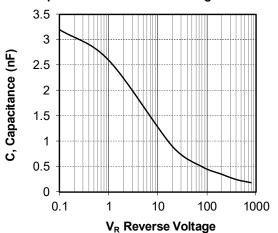


Figure 1-18. Capacitance vs. Reverse Voltage



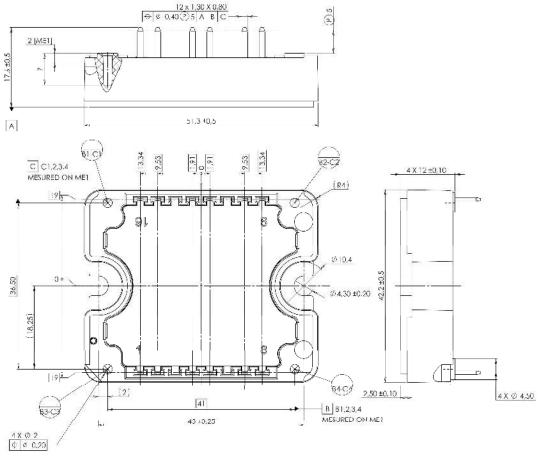
2. Package Specifications

The following section shows the package specification of the MSCSM70VR1M19C1AG device.

2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM70VR1M19C1AG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: See AN3500A—Mounting Instructions for SP1F and SP3F Power Modules for more information.

3. Revision History

Revision	Date	Description
Α	08/2022	Initial Revision

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